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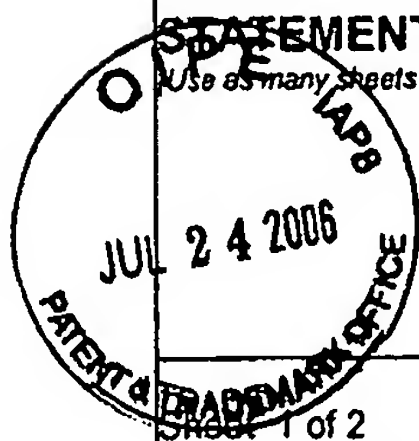
**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(Use as many sheets as necessary)

Complete if Known

Application Number	10/634,174
Filing Date	August 5, 2003
First Named Inventor	Forbes, Leonard
Group Art Unit	2823
Examiner Name	Garcia, Joannie

Attorney Docket No: 1303.102US1



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Examiner Initials *	Cite No *	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
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EXAMINER

Joannie Garcia

DATE CONSIDERED

August 3, 2006

Substitute Disclosure Statement Form (PTO-1448)

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	Group Art Unit	2823
	Examiner Name	Garcia, Joannie
Sheet 2 of 2		Attorney Docket No: 1303.102US1

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
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